

**In the Claims:**

Claims 1-42 (Cancelled).

43. (Original) A thin film transistor backplane, comprising:
- a polyimide substrate;
  - a first passivation layer deposited on a deposition surface of the polyimide substrate;
  - an array of gate electrodes and gate lines patterned on the passivation layer;
  - a gate insulating layer deposited over the array of gate electrodes and gate lines;
  - a semiconducting channel layer deposited over the gate insulating layer;
  - a contact layer deposited on and in contact with the channel layer; and
  - an array of source electrodes, drain electrodes, lines and pads fabricated on and in contact with the contact layer.

Claims 44-95 (Cancelled).